

isc Silicon NPN RF Transistor

2SC4262

DESCRIPTION

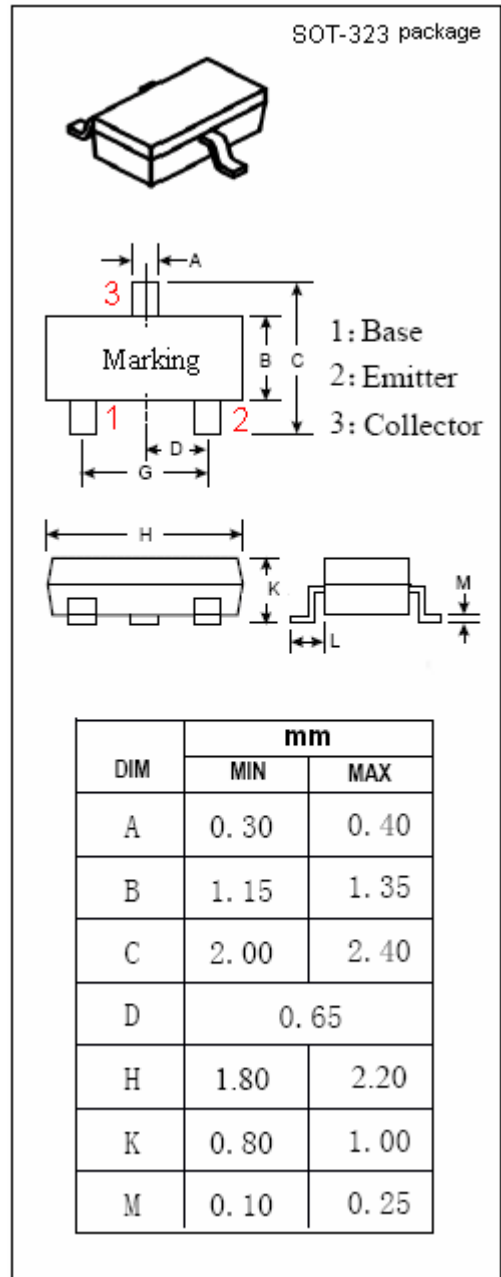
- Low Noise
- High Gain

APPLICATIONS

- Designed for use in UHF~ VHF local oscillator.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-Base Voltage	20	V
V _{CEO}	Collector-Emitter Voltage	15	V
V _{EBO}	Emitter-Base Voltage	3.0	V
I _C	Collector Current-Continuous	50	mA
P _C	Collector Power Dissipation @T _C =25°C	0.1	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=10\mu\text{A}; I_E=0$	20			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=1\text{mA}; R_{BE}=\infty$	15			V
I_{CBO}	Collector Cutoff Current	$V_{CB}=15\text{V}; I_E=0$			0.5	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=3\text{V}; I_C=0$			1.0	μA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=20\text{mA}; I_B=4\text{mA}$			0.5	V
h_{FE}	DC Current Gain	$I_C=5\text{mA}; V_{CE}=10\text{V}$	50		200	
f_T	Current-Gain—Bandwidth Product	$I_C=5\text{mA}; V_{CE}=10\text{V}$	1.4	2.9		GHz
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f=1.0\text{MHz}$			1.0	pF

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